

# MSA1162GT1G

## General Purpose Amplifier Transistors

### PNP Surface Mount

#### Features

- Moisture Sensitivity Level: 1
- This is a Pb-Free Device

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>(BR)CBO</sub>	60	Vdc
Collector-Emitter Voltage	V <sub>(BR)CEO</sub>	50	Vdc
Emitter-Base Voltage	V <sub>(BR)EBO</sub>	7.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Collector Current - Peak	I <sub>C(P)</sub>	200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation	P <sub>D</sub>	200	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

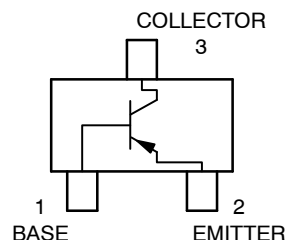
Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 2.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	-	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	7.0	-	Vdc
Collector-Base Cutoff Current (V <sub>CB</sub> = 45 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	0.1	μAdc
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 10 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	0.1	μAdc
(V <sub>CE</sub> = 30 Vdc, I <sub>B</sub> = 0)		-	2.0	μAdc
(V <sub>CE</sub> = 30 Vdc, I <sub>B</sub> = 0, T <sub>A</sub> = 80°C)		-	1.0	mAdc
DC Current Gain (Note 1) (V <sub>CE</sub> = 6.0 Vdc, I <sub>C</sub> = 2.0 mAdc)	h <sub>FE</sub>	200	400	-
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)	V <sub>CE(sat)</sub>	-	0.5	Vdc
Current-Gain-Bandwidth Product (I <sub>C</sub> = 1 mA, V <sub>CE</sub> = 10.0 V, f = 10 MHz)	f <sub>T</sub>	80	-	MHz

1. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.



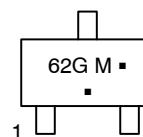
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SC-59  
CASE 318D  
STYLE 1

#### MARKING DIAGRAM



62G = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)  
\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MSA1162GT1G	SC-59 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL ELECTRICAL CHARACTERISTICS

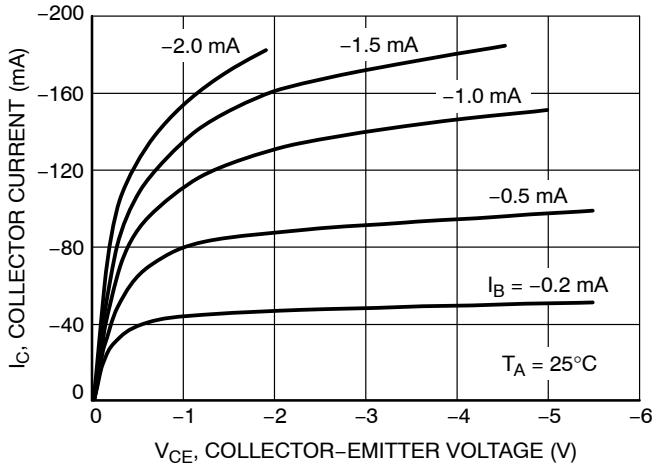


Figure 1. Collector Saturation Region

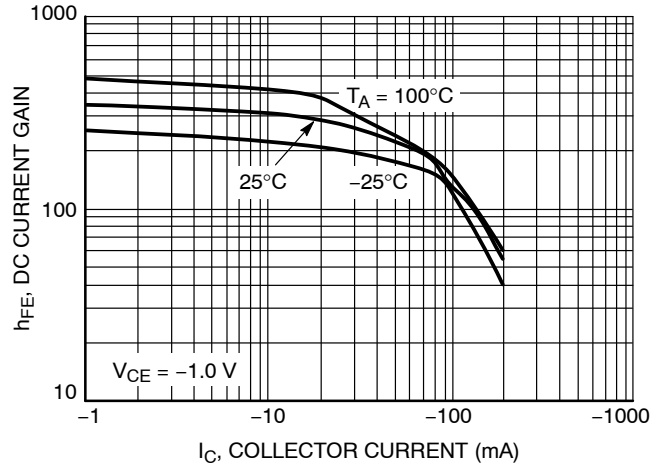


Figure 2. DC Current Gain

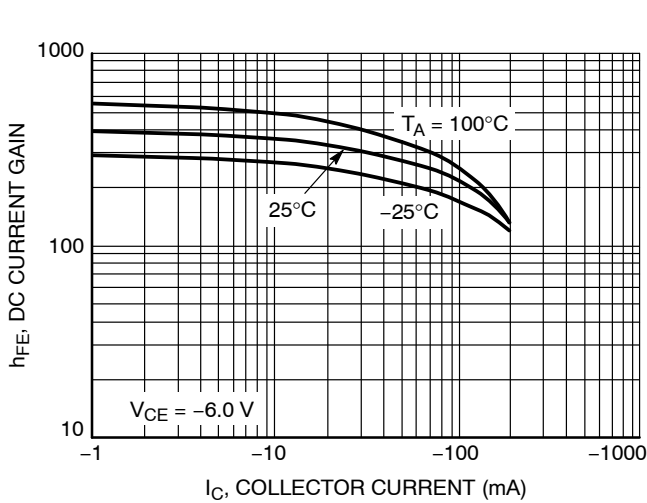


Figure 3. DC Current Gain

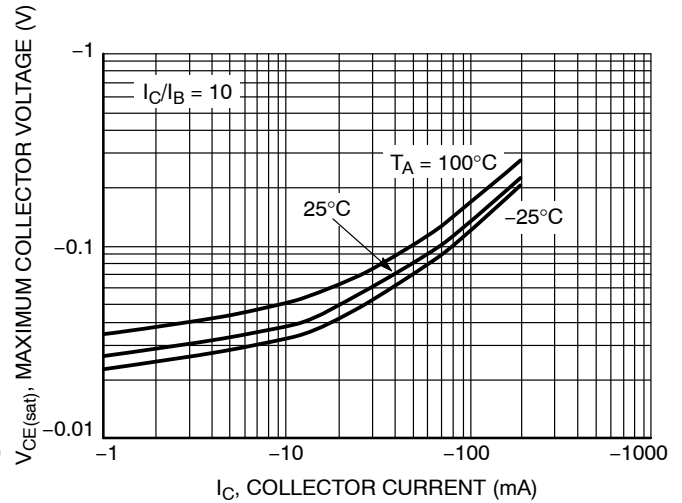


Figure 4.  $V_{CE(sat)}$  versus  $I_C$

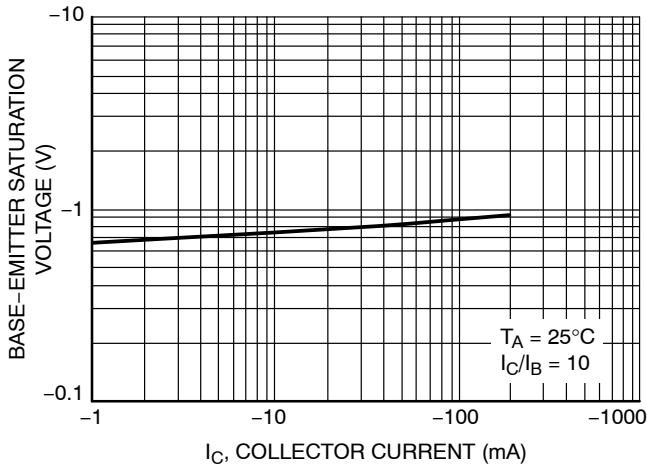


Figure 5.  $V_{BE(sat)}$  versus  $I_C$

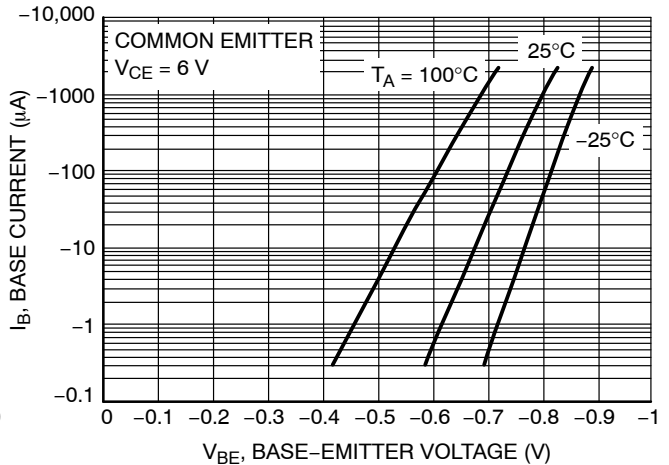


Figure 6. Base-Emitter Voltage

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

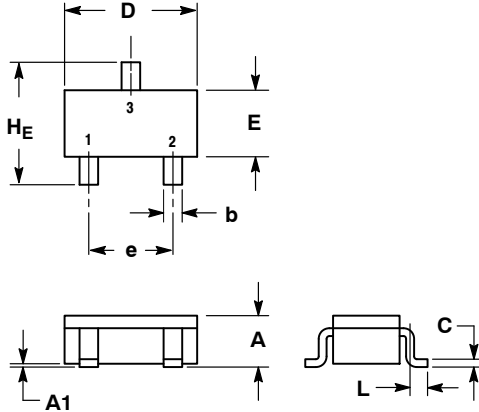
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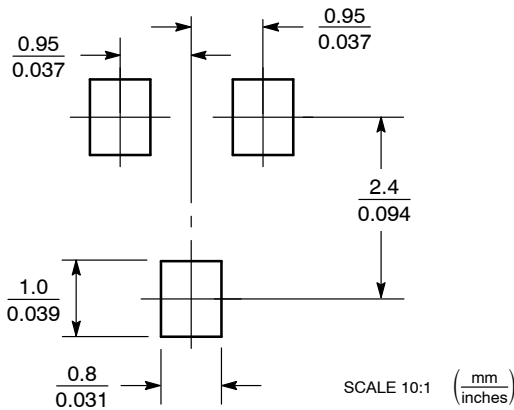
**SC-59**  
CASE 318D-04  
ISSUE H

DATE 28 JUN 2012

SCALE 2:1



### SOLDERING FOOTPRINT\*

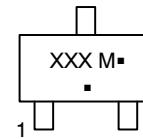


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

### GENERIC MARKING DIAGRAM



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package\*

(\*Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 2:  
PIN 1. ANODE  
2. N.C.  
3. CATHODE

STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 4:  
PIN 1. CATHODE  
2. N.C.  
3. ANODE

STYLE 5:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 6:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE/CATHODE

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